

SKM75GB12V



SEMITRANS® 2

SKM75GB12V

Features

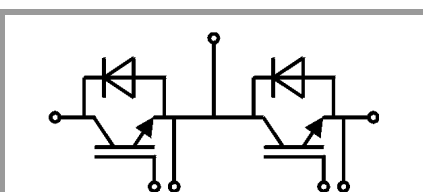
- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V	
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	114	A
		$T_c = 80^\circ\text{C}$	87	A
I_{Cnom}		75	A	
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	225	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 720\text{ V}$	$T_j = 125^\circ\text{C}$	10	μs
	$V_{GE} \leq 20\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
T_j		-40 ... 175	$^\circ\text{C}$	
Inverse diode				
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	97	A
		$T_c = 80^\circ\text{C}$	73	A
I_{Fnom}		75	A	
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	225	A	
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	430	A	
T_j		-40 ... 175	$^\circ\text{C}$	
Module				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	200	A	
T_{stg}		-40 ... 125	$^\circ\text{C}$	
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 75\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.85	2.30	V
		$T_j = 150^\circ\text{C}$	2.25	2.55	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.94	1.04	V
		$T_j = 150^\circ\text{C}$	0.88	0.98	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	12.13	16.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	18.27	20.93	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5.5	6	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	4.5		nF
C_{oes}		$f = 1\text{ MHz}$	0.44		nF
C_{res}		$f = 1\text{ MHz}$	0.442		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		830		nC
R_{Gint}			10.0		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 75\text{ A}$	$T_j = 150^\circ\text{C}$	258		ns
t_r	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	32		ns
E_{on}	$R_{Gon} = 1.3\ \Omega$	$T_j = 150^\circ\text{C}$	6.7		mJ
$t_{d(off)}$	$R_{Goff} = 1.3\ \Omega$	$T_j = 150^\circ\text{C}$	388		ns
t_f	$di/dt_{on} = 3900\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	62		ns
E_{off}	$di/dt_{off} = 1020\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	7.1		mJ
	$du/dt_{off} = 9000\text{ V}/\mu\text{s}$				
$R_{th(j-c)}$	per IGBT		0.38		K/W



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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 75\text{ A}$ $V_{GE} = 0\text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.17	2.49	V
		$T_j = 150^\circ\text{C}$		2.11	2.42	V
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		11.6	13.2	m Ω
		$T_j = 150^\circ\text{C}$		16.1	17.6	m Ω
I_{RRM}	$I_F = 75\text{ A}$	$T_j = 150^\circ\text{C}$		85		A
Q_{rr}	$di/dt_{off} = 2950\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		10		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		4.2		mJ
$R_{th(j-c)}$	per diode				0.58	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.65		m Ω
		$T_c = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.04	0.05	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



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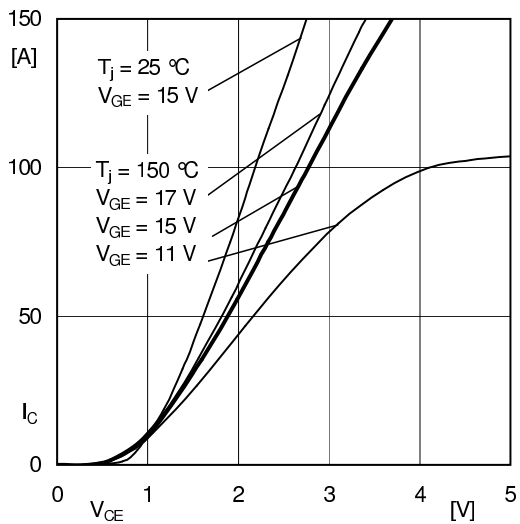


Fig. 1: Typ. output characteristic, inclusive R_{CC+EE}

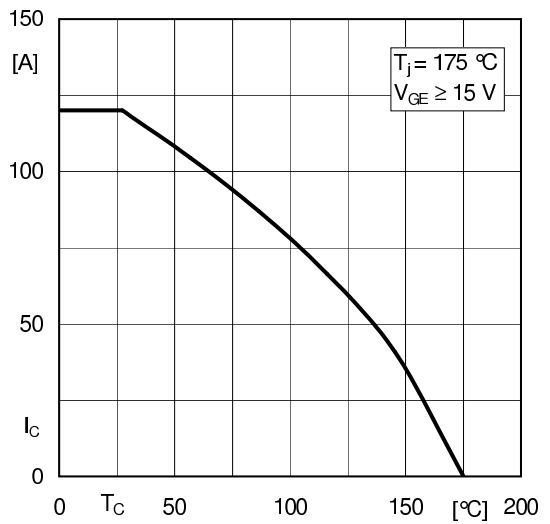


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

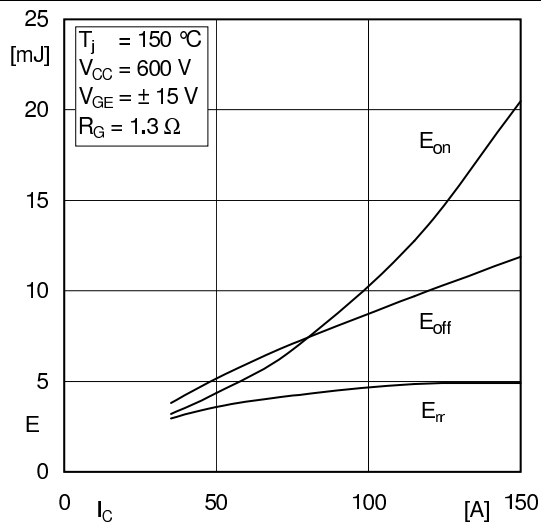


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

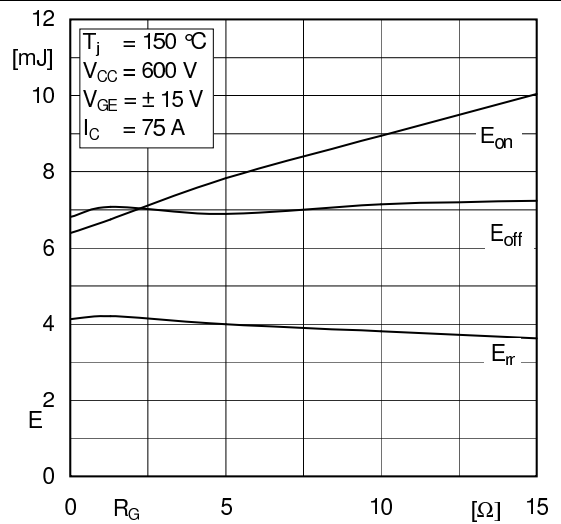


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

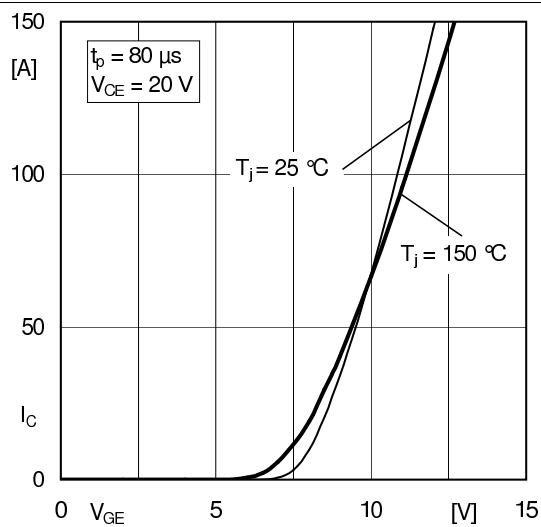


Fig. 5: Typ. transfer characteristic

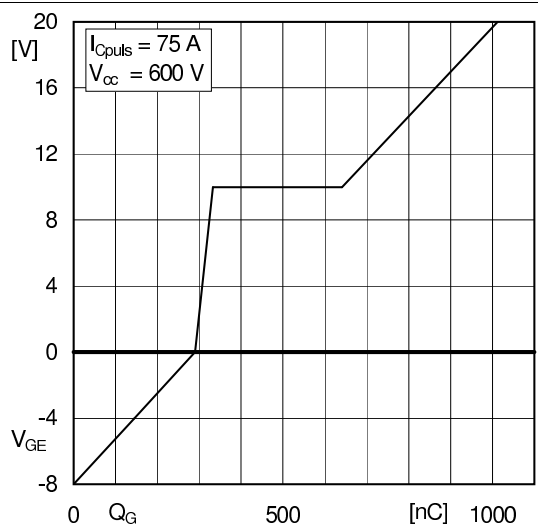


Fig. 6: Typ. gate charge characteristic

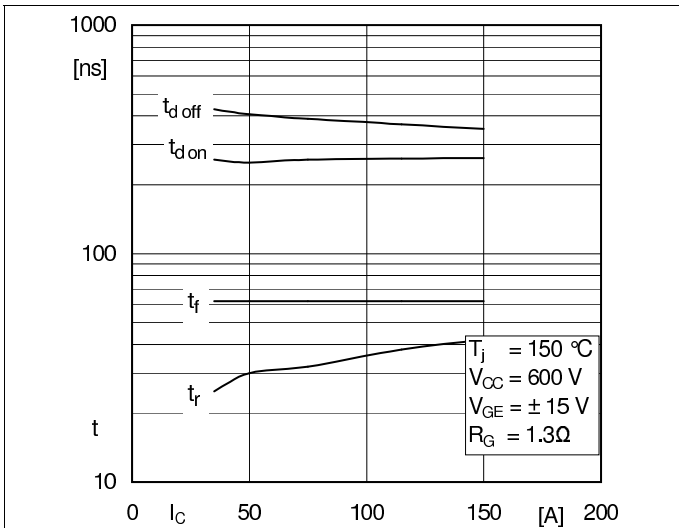


Fig. 7: Typ. switching times vs. I_C

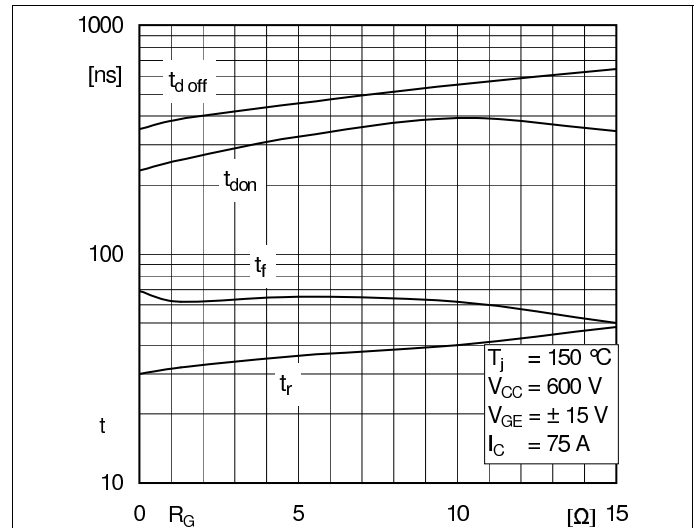


Fig. 8: Typ. switching times vs. gate resistor R_G

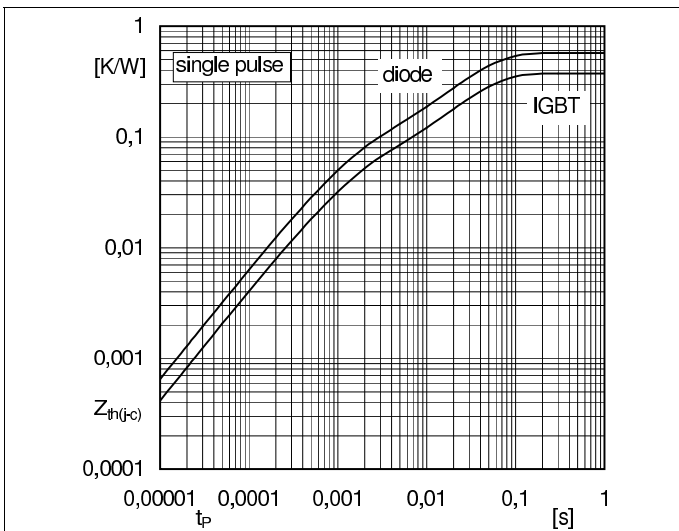


Fig. 9: Transient thermal impedance

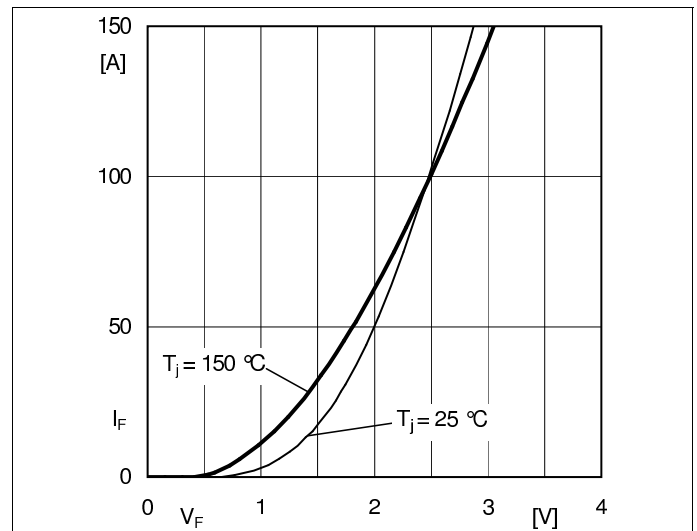


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}

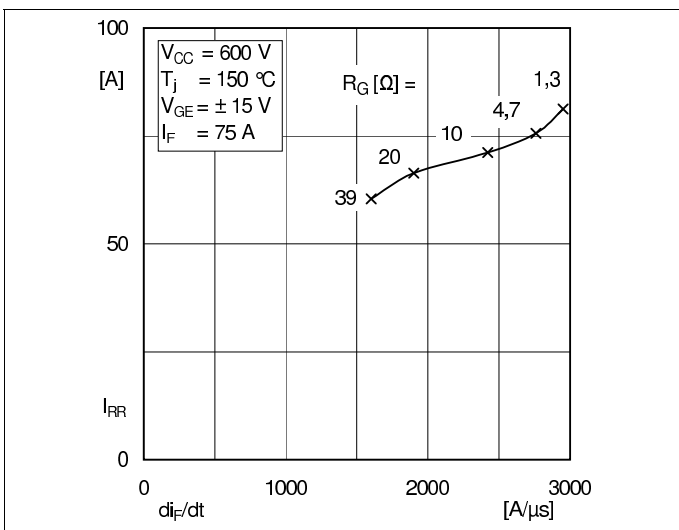


Fig. 11: CAL diode peak reverse recovery current

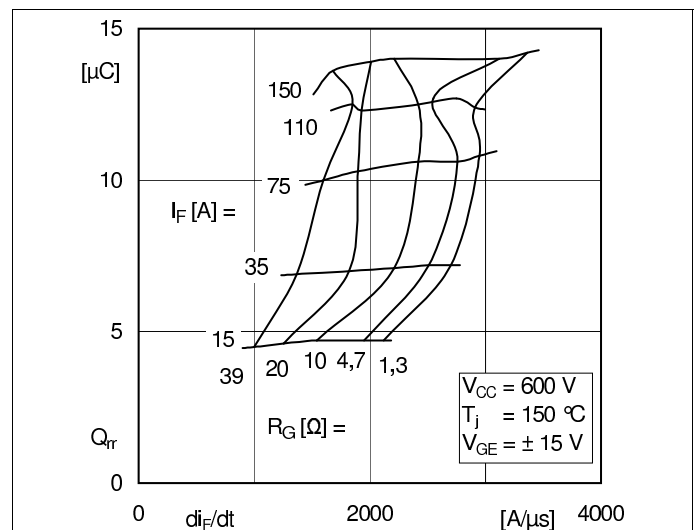


Fig. 12: Typ. CAL diode peak reverse recovery charge

